



# **Global Communication Semiconductors, LLC**

Corporate & Foundry

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## **Device Modeling Engineer**

1. Perform device characterization, simulation, non-linear device modeling in GaN HEMT, InGaP and InP HBT, III-V varactor, diodes and resonators.
2. Support GaN HEMT technology development and problem solving.
3. Perform load pull, noise parameters characterization of III-V semiconductor devices.
4. Interact with customers and process engineers to define and optimize device models.

Requires Master's degree in Electrical Engineering or a related field.

Requires two years of experience in job offered or in III-V semiconductors. A Ph.D. degree is acceptable in lieu of the two years' experience.

Requires R&D experience in using simulators to understand device physics, GaN High Electron Mobility Transistors (HEMT), and characterization and modeling of resonators.

Location: Torrance, CA

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